

ZXTD1M832

MPPS™ Miniature Package Power Solutions DUAL 12V PNP LOW SATURATION SWITCHING TRANSISTOR

SUMMARY

$V_{CE0} = -12V$; $R_{SAT} = 60m\Omega$; $I_C = -4A$

DESCRIPTION

Packaged in the innovative 3mm x 2mm MLP (Micro Leaded Package) outline, these new 4th generation low saturation dual transistors offer extremely low on state losses making them ideal for use in DC-DC circuits and various driving and power management functions.

Additionally users gain several other **key benefits**:

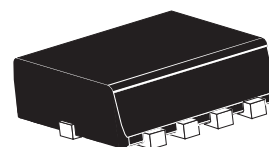
Performance capability equivalent to much larger packages

Improved circuit efficiency & power levels

PCB area and device placement savings

Lower package height (nom 0.9mm)

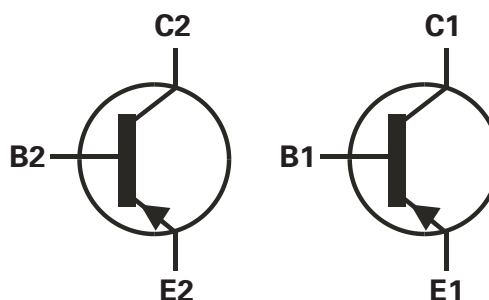
Reduced component count



3mm x 2mm (Dual die) MLP

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage (-140mV @ -1A)
- h_{FE} characterised up to -10A
- $I_C = -4A$ Continuous Collector Current
- 3mm x 2mm MLP



APPLICATIONS

- DC - DC Converters (FET Drivers)
- Charging circuits
- Power switches
- Motor control

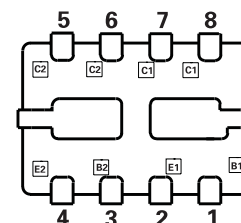
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXTD1M832TA	7"	8mm	3000
ZXTD1M832TC	13"	8mm	10000

DEVICE MARKING

D11

PINOUT



3mm x 2mm MLP
underside view

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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-7.5	V
Peak Pulse Current	I_{CM}	-12	A
Continuous Collector Current	I_C	-4	A
Continuous Collector Current (b)	I_C	-4.4	A
Base Current	I_B	-1000	mA
Power Dissipation at $T_A=25^{\circ}\text{C}$ (a)(f) Linear Derating Factor	P_D	1.5 12	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (b)(f) Linear Derating Factor	P_D	2.45 19.6	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (c)(f) Linear Derating Factor	P_D	1 8	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (d)(f) Linear Derating Factor	P_D	1.13 9	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (d)(g) Linear Derating Factor	P_D	1.7 13.6	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ (e)(g) Linear Derating Factor	P_D	3 24	W mW/ $^{\circ}\text{C}$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}\text{C}$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	$R_{\theta JA}$	83.3	$^{\circ}\text{C/W}$
Junction to Ambient (b)(f)	$R_{\theta JA}$	51	$^{\circ}\text{C/W}$
Junction to Ambient (c)(f)	$R_{\theta JA}$	125	$^{\circ}\text{C/W}$
Junction to Ambient (d)(f)	$R_{\theta JA}$	111	$^{\circ}\text{C/W}$
Junction to Ambient (d)(g)	$R_{\theta JA}$	73.5	$^{\circ}\text{C/W}$
Junction to Ambient (e)(g)	$R_{\theta JA}$	41.7	$^{\circ}\text{C/W}$

Notes

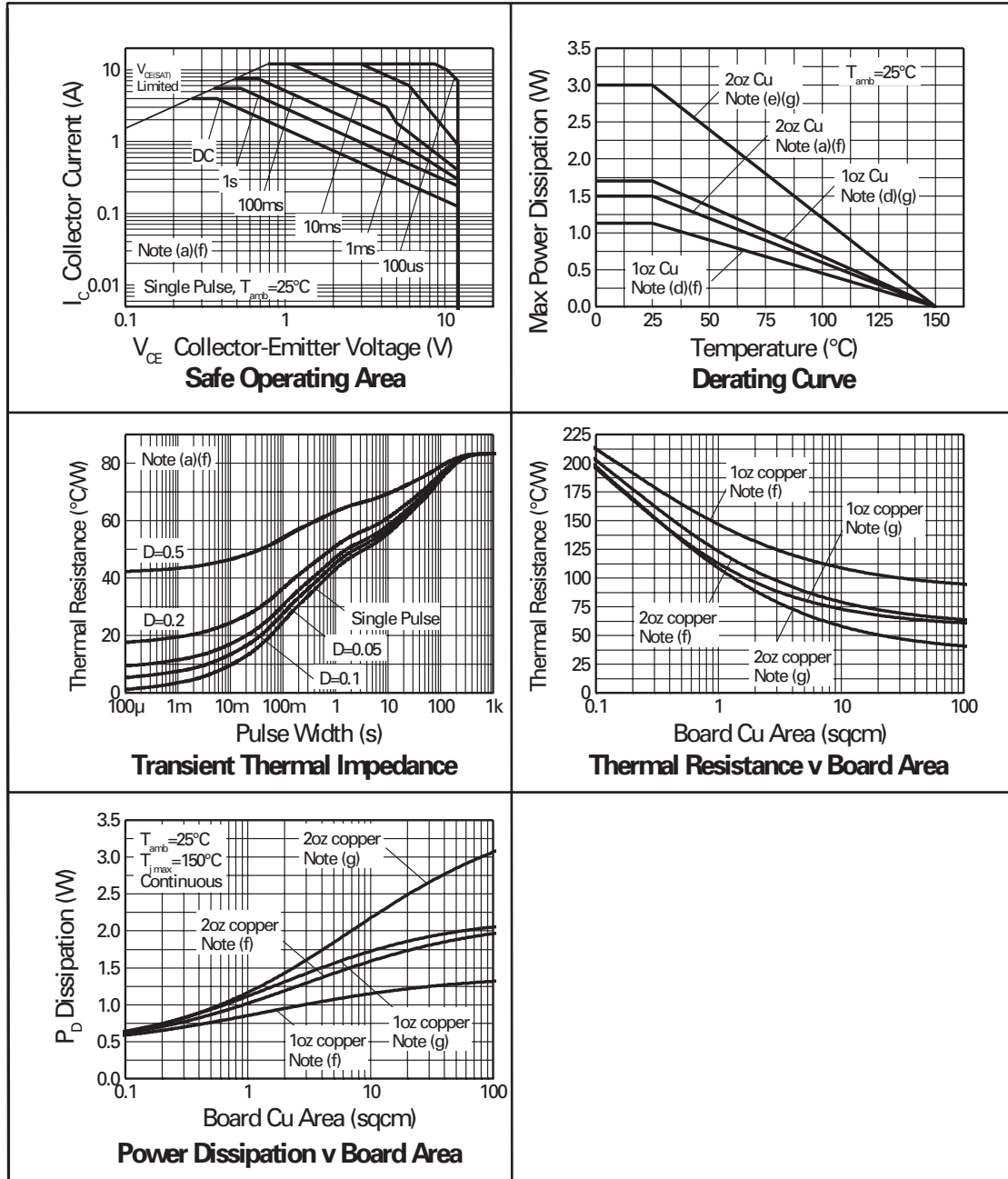
- (a) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (b) Measured at $t < 5$ secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (c) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with minimal lead connections only**.
- (d) For a dual device surface mounted on 10 sq cm single sided 1oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (e) For a dual device surface mounted on 85 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (f) For a dual device with one active die.
- (g) For dual device with 2 active die running at equal power.
- (h) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.
- (i) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper 1 oz weight, 1mm wide tracks and one half of the device active is $R_{th} = 250^{\circ}\text{C/W}$ giving a power rating of $P_{tot} = 500\text{mW}$.



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TYPICAL CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-20	-35		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-12	-25		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-7.5	8.5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-25	nA	$V_{CB} = -16\text{V}$
Emitter Cut-Off Current	I_{EBO}			-25	nA	$V_{EB} = -6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			-25	nA	$V_{CES} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-10	-17	mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$
			-100	-140	mV	$I_C = -1\text{A}, I_B = -10\text{mA}^*$
			-100	-150	mV	$I_C = -1.5\text{A}, I_B = -50\text{mA}^*$
			-195	-300	mV	$I_C = -3\text{A}, I_B = -50\text{mA}^*$
			-240	-300	mV	$I_C = -4\text{A}, I_B = -150\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.97	-1.050	V	$I_C = -4\text{A}, I_B = 150\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.87	-0.950	V	$I_C = -4\text{A}, V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300	475			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$
		300	450			$I_C = -0.1\text{A}, V_{CE} = -2\text{V}^*$
		180	275			$I_C = -2.5\text{A}, V_{CE} = -2\text{V}^*$
		60	100			$I_C = -8\text{A}, V_{CE} = -2\text{V}^*$
		45	70			$I_C = -10\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T	100	110		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		21	30	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		70		ns	$V_{CC} = -6\text{V}, I_C = -2\text{A}$
Turn-Off Time	$t_{(off)}$		130		ns	$I_{B1} = I_{B2} = -50\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

